PLASMA PROCESSING APPARATUS

Abstract

Provided is a technique for stabilizing a plasma. There is provided a plasma processing apparatus including a chamber; a substrate support placed in the chamber and including at least one lower electrode; an upper electrode placed above the substrate support; an RF signal generator electrically connected to any of the at least one lower electrode or the upper electrode, and configured to generate an RF signal for generating a plasma in the chamber; a first voltage signal generator electrically connected to any of the at least one lower electrode and configured to generate a first voltage signal, the first voltage signal having a sequence of first voltage pulses; a second voltage signal generator electrically connected to the upper electrode and configured to generate a second voltage signal; a capacitor; and a rectifying element including a first electrode and a second electrode, the first electrode being electrically connected to a node between the upper electrode and the second voltage signal generator, and the second electrode being electrically connected to a ground potential via the capacitor.

Fig. 5